

The MPSA12 is NPN silicon darlington transistor designed for preamplifier input applications requiring input impedance of several megohms.

T0-92



EBC

ABSOLUTE MAXIMUM RATINGS

Collector-Emitter Voltage	V _{CES}	20V
Emitter-Base Voltage	V _{EB0}	10V
Collector Current	I _C	500mA
Total Power Dissipation	P _{tot}	625mW
Operating Junction & Storage Temperature	T _j , T _{stg}	-55 to +150°C

ELECTRICAL CHARACTERISTICS (T_a=25°C)

PARAMETER	SYMBOL	MIN	MAX	UNIT	TEST CONDITIONS
Collector-Emitter Breakdown Voltage	BV _{CES}	20		V	I _C =100μA I _B =0
Collector Cutoff Current	I _{CES}		100	nA	V _{CE} =15V V _{BE} =0
Collector Cutoff Current	I _{CB0}		100	nA	V _{CB} =15V I _E =0
Emitter Cutoff Current	I _{EB0}		100	nA	V _{EB} =10V I _C =0
D.C. Current Gain	HFE	20K			I _C =10mA V _{CE} =5V
Collector-Emitter Saturation Voltage	V _{CE(sat)}		1	V	I _C =10mA I _B =10μA
Base-Emitter Voltage	V _{BE}		1.4	V	I _C =10mA V _{CE} =5V
Output Capacitance	C _{ob}	8 typ		pF	V _{CB} =10V f=100KHz



MICRO ELECTRONICS LTD. 美科有限公司

38 Hung To Road, Kwun Tong, Kowloon, Hong Kong. Cable: Microtron, Hong Kong. Telex: 43510 Micro Hx.
P.O. Box 9477, Kwun Tong. Tel: 3-430181-6, 3-893363, 3-892423, 3-898221

FAX: 3-410321